DK51

NPN Silicon High Power Switching Transistor

Features:

1. Good switching character. Excellent capacity in anti-burnout.
2. Good temperature stability. Small saturation voltage drop.
3. Implementation of standards: GJB33A -97, QZJ840611A, QZJ840611
4. Use for high power switch circuit,switching voltage-stabilized sourcefy circuit.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA: **(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications							Test Condition
			A	B	C	D	E	F	G	
Total Dissipation	P_{tot}	W	50							Tc:75°C
Max. Collector Current	I_{CM}	A	10							
Junction Temperature	T_{jm}	°C	175							
Storage Temperature	T_{stg}	°C	-55~+175							
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	30	50	80	110	150	200	250	I_C=3mA
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	5							I_E=3mA
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.5							I_C=2.5A,I_B=0.25A
Collector-Emitter Leakage Current	I_{CEO}	mA	3.0							V_{CE}=A:20V,B:30V,C:50V, D~G:100V
DC Current Gain	h_{FE}		10							V_{CE}=5V,I_C=2.5A
Delay Time	t_d	us	0.1							V_{CE}=25V
Rise Time	t_r	us	1.5							I_C=2.5A
Storage Time	t_s	us	1.5							I_{B1}=0.25A
Fall Time	t_f	us	0.8							I_{B2}=-0.25A

Outline and Dimensions: